

Features

- Interdigitated amplifying gates
- Fast turn-on and high dI/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$	1460A
V_{DRM}/V_{RRM}	800~1800V
t_q	18~50μs
I_{TSM}	16kA
I^2t	1280 10³ A²s



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	125			1460	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	125	800		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			100	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			16	kA
I^2t	I^2t for fusing coordination					1280	$A^2s^*10^3$
V_{TO}	Threshold voltage		125			1.51	V
r_T	On-state slope resistance					0.32	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=3000A$, $F=26kN$	25			3.15	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 2000A, Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1200	A/μs
Q_{rr}	Recovery charge	$I_{TM}=1500A$, tp=2000μs, $di/dt=-60A/\mu s$, $V_R=50V$	125		750		μC
t_q	Circuit commutated turn-off time	$I_{TM}=1000A$, tp=1000μs, $V_R=50V$ $dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	125	18		50	μs
I_{GT}	Gate trigger current			40		300	mA
V_{GT}	Gate trigger voltage	$V_A=12V$, $I_A=1A$	25	0.9		3.0	V
I_H	Holding current			20		500	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-c)}$	Thermal resistance Junction to case					0.018	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink	At 180° sine double side cooled Clamping force 26kN				0.004	
F_m	Mounting force			21		30	kN
T_{stg}	Stored temperature			-40		130	°C
W_t	Weight				590		g
Outline				KT54cT55			

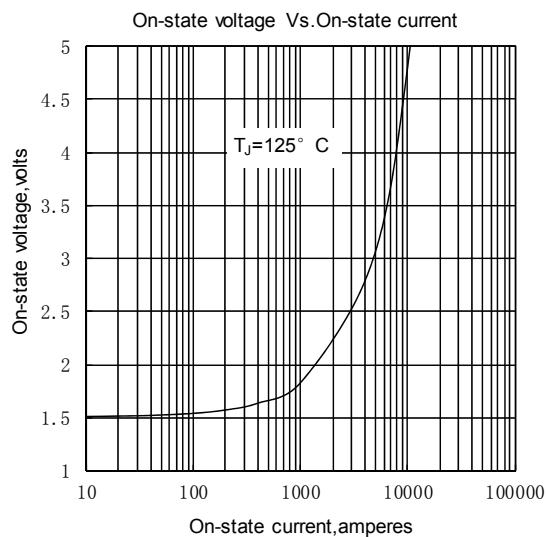


Fig. 1

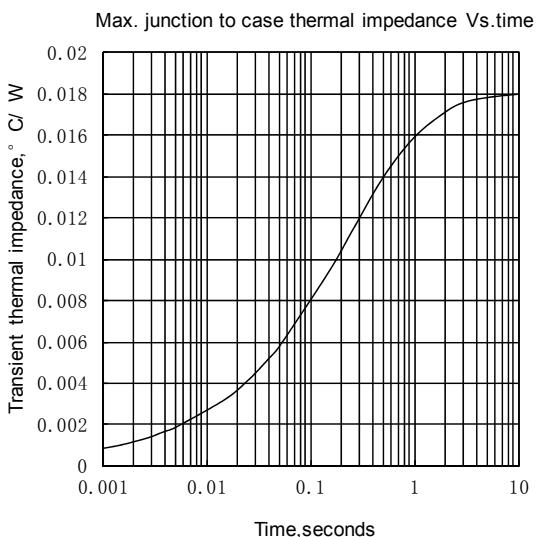


Fig. 2

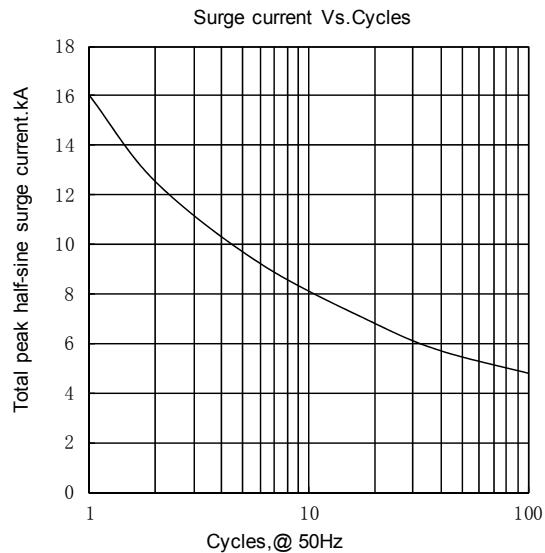


Fig. 3

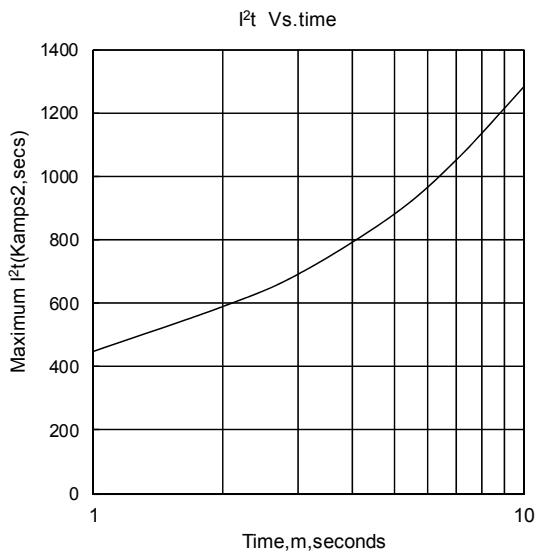


Fig. 4

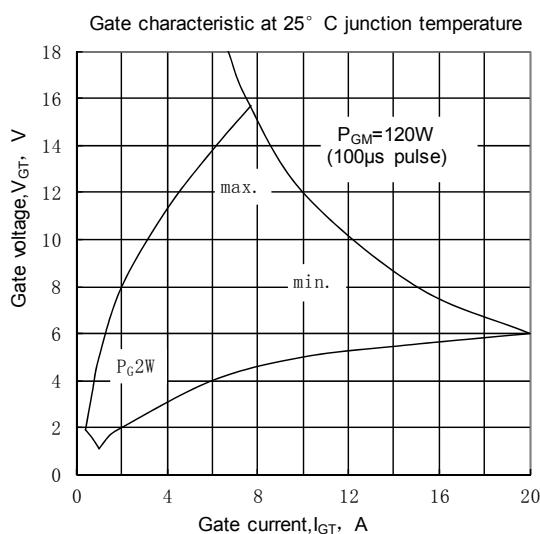


Fig. 5

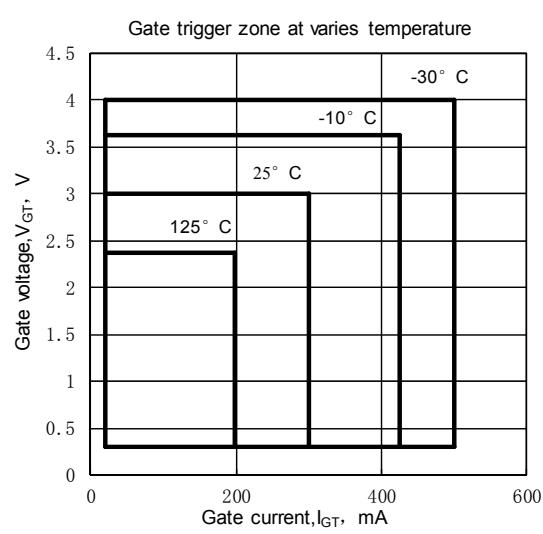


Fig. 6

Outline: